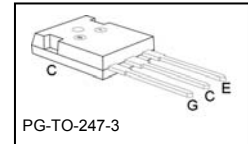
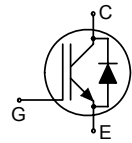


Reverse Conducting IGBT with monolithic body diode

Features:

- 1.5V Forward voltage of monolithic body Diode
- Full Current Rating of monolithic body Diode
- Specified for $T_{jmax} = 175^{\circ}\text{C}$
- Trench and Fieldstop technology for 1000 V applications offers :
 - very tight parameter distribution
 - high ruggedness, temperature stable behavior
 - easy parallel switching capability due to positive temperature coefficient in $V_{CE(sat)}$
- Low EMI
- Qualified according to JEDEC¹ for target applications
- Pb-free lead plating; RoHS compliant



Applications:

- Microwave Oven
- Soft Switching Applications

Type	V_{CE}	I_C	$V_{CE(sat), T_j=25^{\circ}\text{C}}$	$T_{j,max}$	Marking	Package
IHW30N100R	1000V	30A	1.5V	175°C	H30R100	PG-TO-247-3

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CE}	1000	V
DC collector current	I_C	60 30	A
$T_C = 25^{\circ}\text{C}$			
$T_C = 100^{\circ}\text{C}$			
Pulsed collector current, t_p limited by T_{jmax}	I_{Cpuls}	90	
Turn off safe operating area $V_{CE} \leq 1000\text{V}$, $T_j \leq 175^{\circ}\text{C}$	-	90	
Diode forward current	I_F	60 30	
$T_C = 25^{\circ}\text{C}$			
$T_C = 100^{\circ}\text{C}$			
Diode pulsed current, t_p limited by T_{jmax}	I_{Fpuls}	90	
Gate-emitter voltage	V_{GE}	± 20	V
Transient Gate-emitter voltage ($t_p < 5$ ms)		± 25	
Power dissipation, $T_C = 25^{\circ}\text{C}$	P_{tot}	412	W
Operating junction temperature	T_j	-40...+175	°C
Storage temperature	T_{stg}	-55...+175	°C
Soldering temperature, 1.6mm (0.063 in.) from case for 10s	-	260	

¹ J-STD-020 and JESD-022

Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic				
IGBT thermal resistance, junction – case	R_{thJC}		0.36	K/W
Diode thermal resistance, junction – case	R_{thJCD}		0.36	
Thermal resistance, junction – ambient	R_{thJA}		40	

Electrical Characteristic, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=500\mu A$	1000	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE} = 15V, I_C=30A$ $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$ $T_j=175^\circ\text{C}$	-	1.5	1.7	
Diode forward voltage	V_F	$V_{GE}=0V, I_F=30A$ $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$ $T_j=175^\circ\text{C}$	-	1.5	1.7	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=700\mu A, V_{CE}=V_{GE}$	5.1	5.8	6.4	
Zero gate voltage collector current	I_{CES}	$V_{CE}=1000V, V_{GE}=0V$ $T_j=25^\circ\text{C}$ $T_j=175^\circ\text{C}$	-	-	5	μA
Gate-emitter leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=20V$	-	-	600	
Transconductance	g_{fs}	$V_{CE}=20V, I_C=30A$	-	56	-	S

Dynamic Characteristic

Input capacitance	C_{iss}	$V_{CE}=25V,$ $V_{GE}=0V,$ $f=1\text{MHz}$	-	2791	-	pF
Output capacitance	C_{oss}		-	82	-	
Reverse transfer capacitance	C_{rss}		-	78	-	
Gate charge	Q_{Gate}	$V_{CC}=800V, I_C=30A$ $V_{GE}=15V$	-	209	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E		-	13	-	nH

Switching Characteristic, Inductive Load, at $T_j=25^\circ\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
IGBT Characteristic						
Turn-off delay time	$t_{d(\text{off})}$	$T_j=25^\circ\text{C}$, $V_{CC}=600\text{V}$, $I_C=30\text{A}$, $V_{GE}=0/15\text{V}$, $R_G=26\Omega$,	-	846	-	mJ
Fall time	t_f		-	33.3	-	
Turn-on energy	E_{on}		-	-	-	
Turn-off energy	E_{off}		-	2.1	-	
Total switching energy	E_{ts}		-	-	-	

Switching Characteristic, Inductive Load, at $T_j=175^\circ\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
IGBT Characteristic						
Turn-off delay time	$t_{d(\text{off})}$	$T_j=175^\circ\text{C}$ $V_{CC}=600\text{V}$, $I_C=30\text{A}$, $V_{GE}=0/15\text{V}$, $R_G=26\Omega$	-	948	-	mJ
Fall time	t_f		-	40.4	-	
Turn-on energy	E_{on}		-	-	-	
Turn-off energy	E_{off}		-	2.86	-	
Total switching energy	E_{ts}		-	-	-	

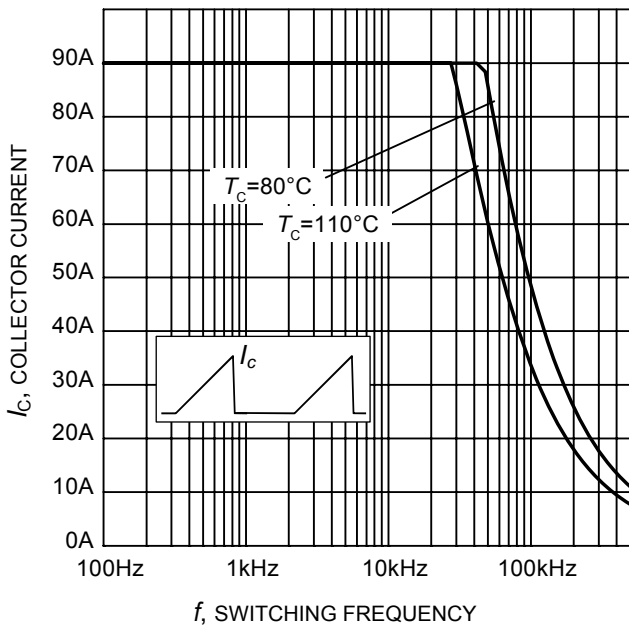


Figure 1. Collector current as a function of switching frequency for triangular current ($E_{on} = 0$, hard turn-off)
 ($T_j \leq 175^\circ\text{C}$, $D = 0.5$, $V_{CE} = 400\text{V}$, $V_{GE} = 0/+15\text{V}$, $R_G = 26\Omega$)

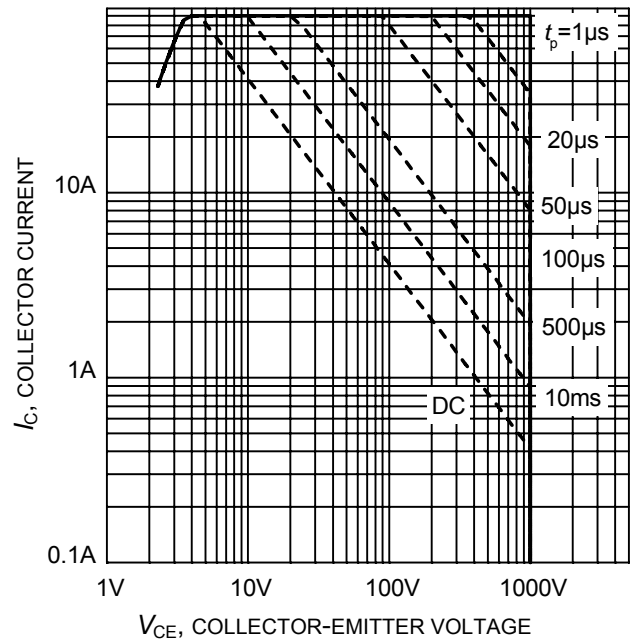


Figure 2. Safe operating area
 ($D = 0$, $T_C = 25^\circ\text{C}$, $T_j \leq 175^\circ\text{C}$; $V_{GE} = 15\text{V}$)

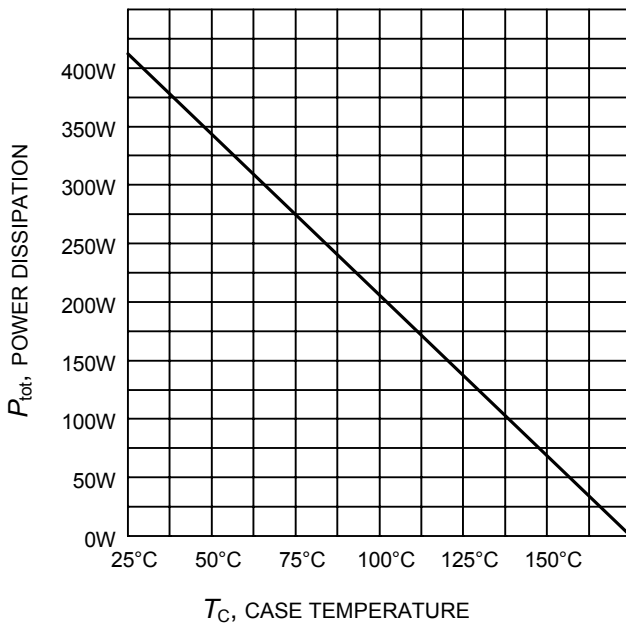


Figure 3. Power dissipation as a function of case temperature
 ($T_j \leq 175^\circ\text{C}$)

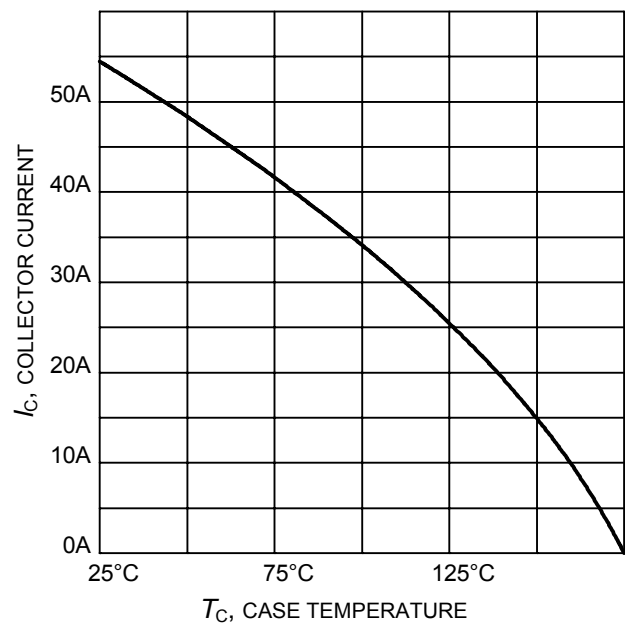


Figure 4. Collector current as a function of case temperature
 ($V_{GE} \geq 15\text{V}$, $T_j \leq 175^\circ\text{C}$)

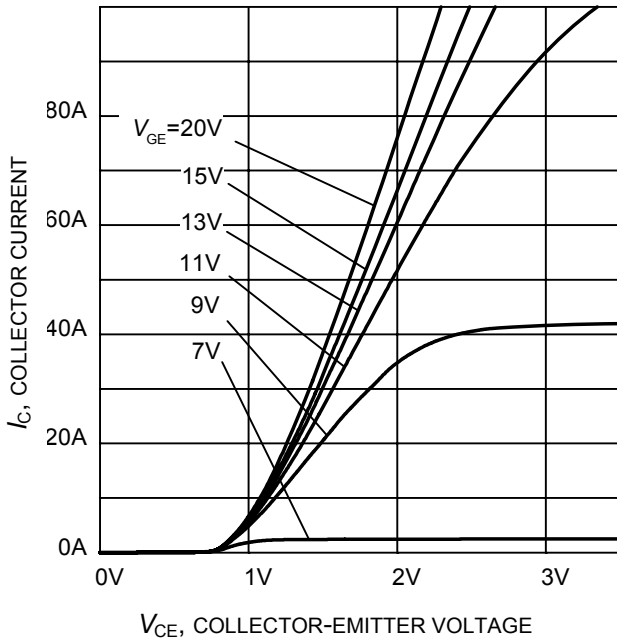


Figure 5. Typical output characteristic
($T_j = 25^\circ\text{C}$)

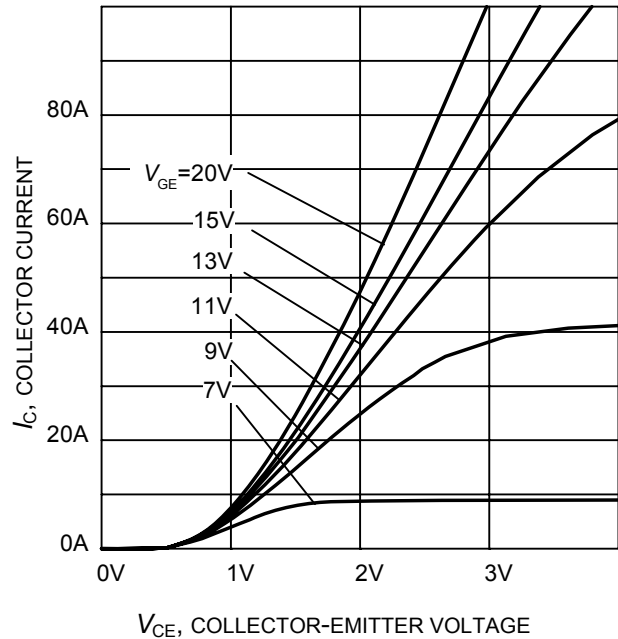


Figure 6. Typical output characteristic
($T_j = 175^\circ\text{C}$)

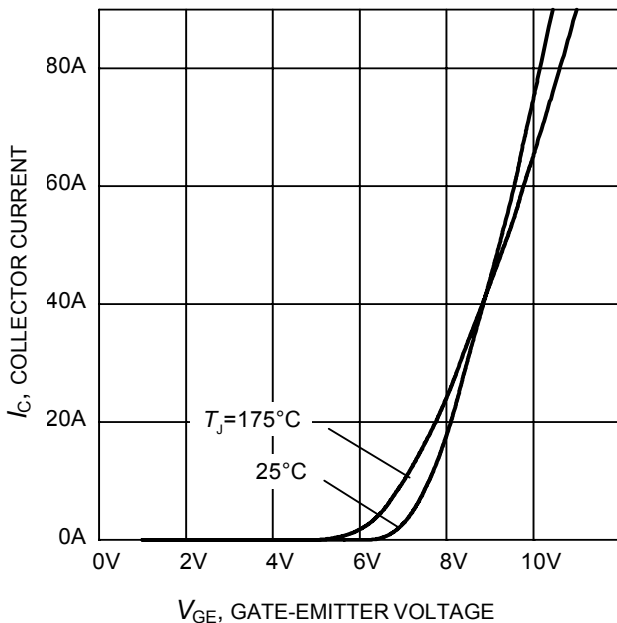


Figure 7. Typical transfer characteristic
($V_{CE} = 20\text{V}$)

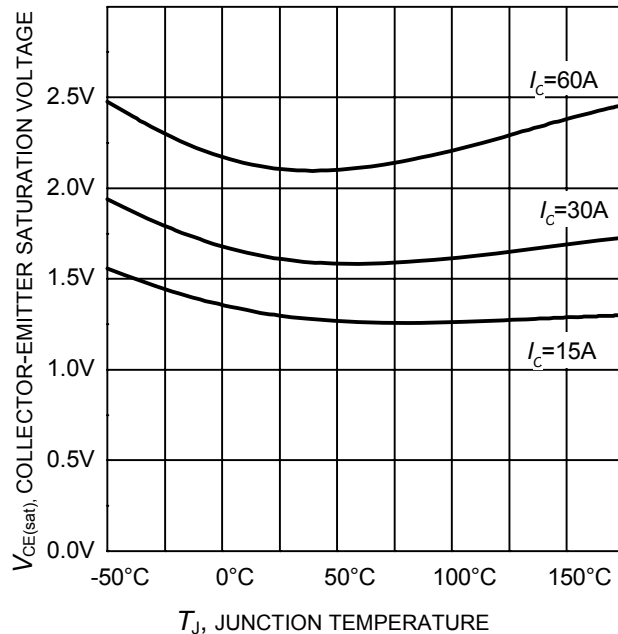


Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature
($V_{GE} = 15\text{V}$)

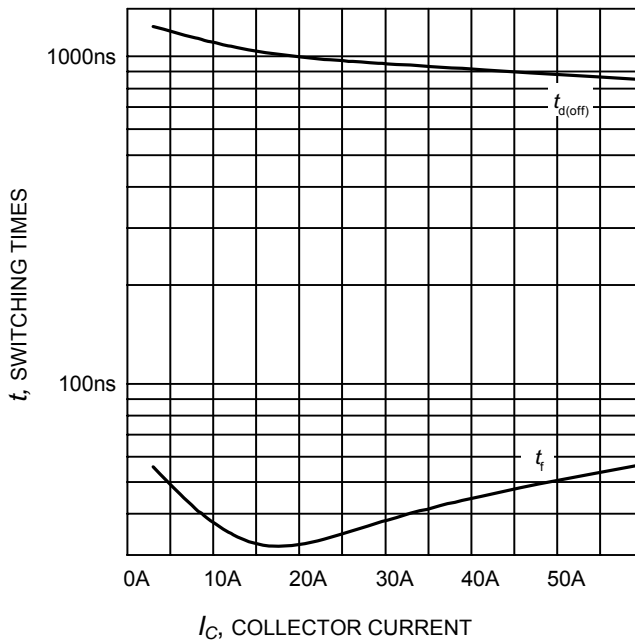


Figure 9. Typical switching times as a function of collector current
 (inductive load, $T_J=175^\circ\text{C}$,
 $V_{CE} = 600\text{V}$, $V_{GE} = 0/15\text{V}$, $R_G=26\Omega$,
 Dynamic test circuit in Figure E)

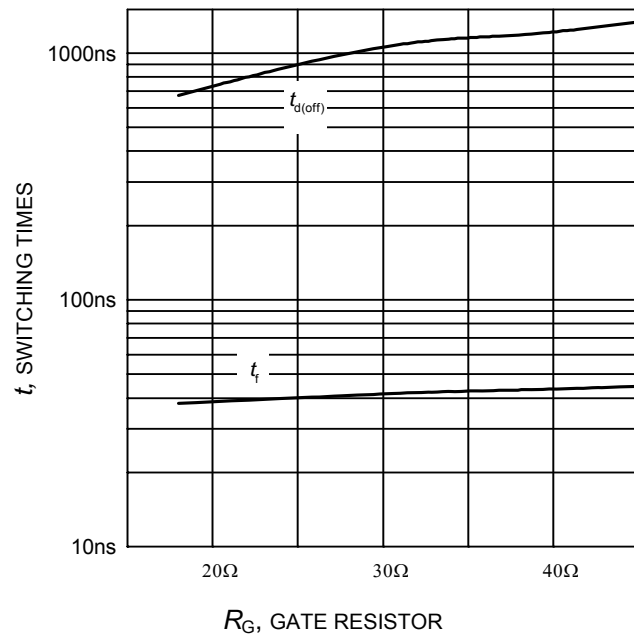


Figure 10. Typical switching times as a function of gate resistor
 (inductive load, $T_J = 175^\circ\text{C}$,
 $V_{CE} = 600\text{V}$, $V_{GE} = 0/15\text{V}$, $I_C = 30\text{A}$,
 Dynamic test circuit in Figure E)

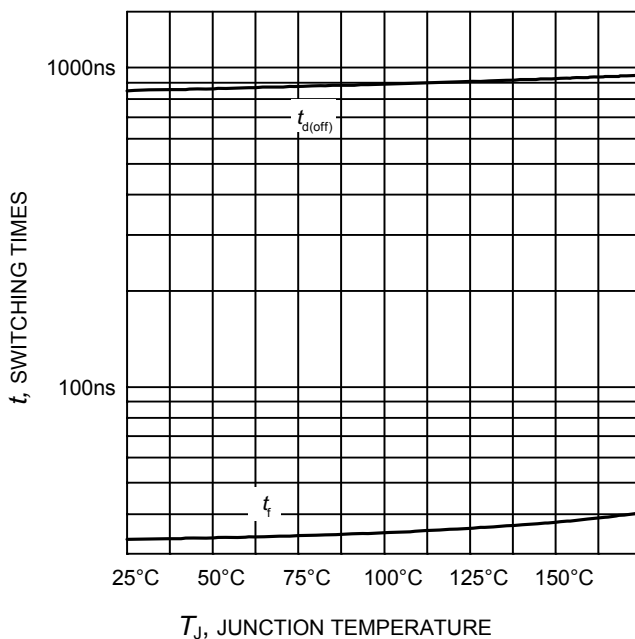


Figure 11. Typical switching times as a function of junction temperature
 (inductive load, $V_{CE} = 600\text{V}$,
 $V_{GE} = 0/15\text{V}$, $I_C = 30\text{A}$, $R_G=26\Omega$,
 Dynamic test circuit in Figure E)

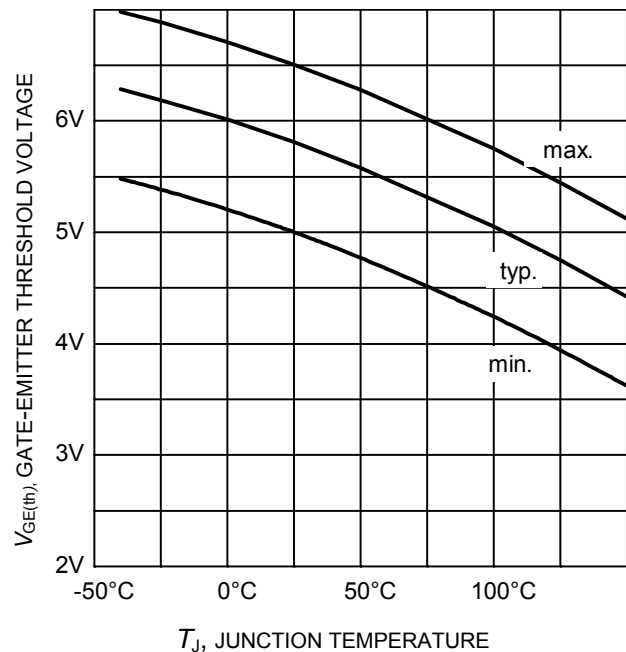


Figure 12. Gate-emitter threshold voltage as a function of junction temperature
 ($I_C = 0.7\text{mA}$)

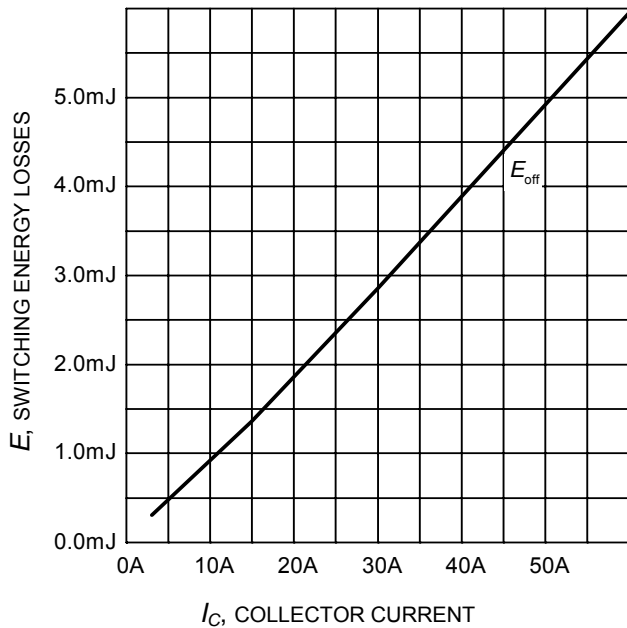


Figure 13. Typical switching energy losses as a function of collector current
 (inductive load, $T_J = 175^\circ\text{C}$, $V_{CE} = 600\text{V}$, $V_{GE} = 0/15\text{V}$, $R_G = 26\Omega$, Dynamic test circuit in Figure E)

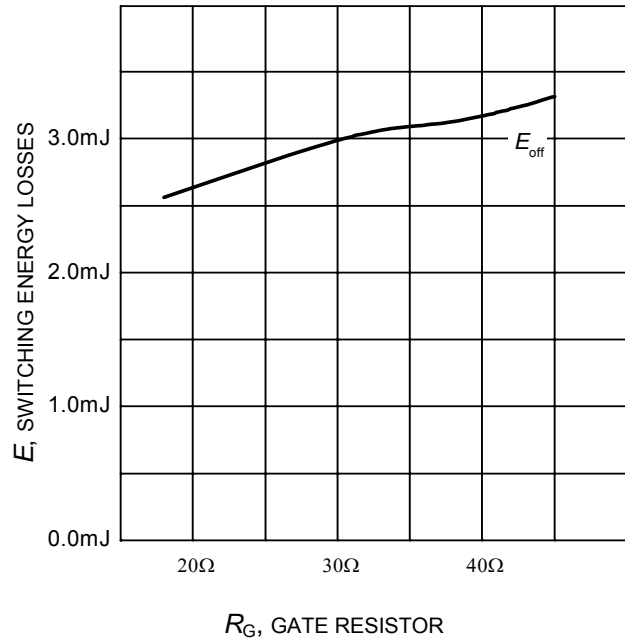


Figure 14. Typical switching energy losses as a function of gate resistor
 (inductive load, $T_J = 175^\circ\text{C}$, $V_{CE} = 600\text{V}$, $V_{GE} = 0/15\text{V}$, $I_C = 30\text{A}$, Dynamic test circuit in Figure E)

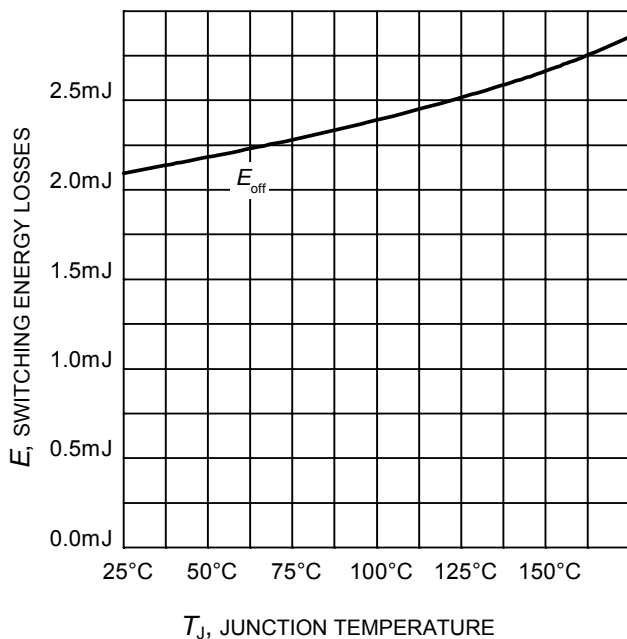


Figure 15. Typical switching energy losses as a function of junction temperature
 (inductive load, $V_{CE} = 600\text{V}$, $V_{GE} = 0/15\text{V}$, $I_C = 30\text{A}$, $R_G = 26\Omega$, Dynamic test circuit in Figure E)

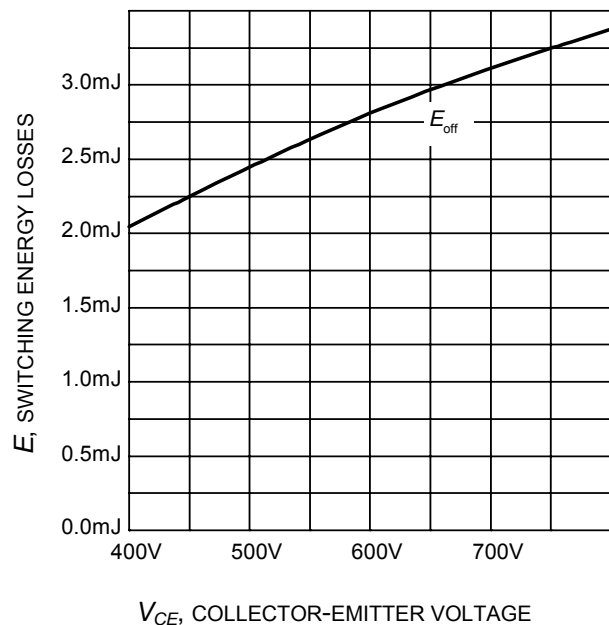


Figure 16. Typical switching energy losses as a function of collector emitter voltage
 (inductive load, $T_J = 175^\circ\text{C}$, $V_{GE} = 0/15\text{V}$, $I_C = 30\text{A}$, $R_G = 26\Omega$, Dynamic test circuit in Figure E)

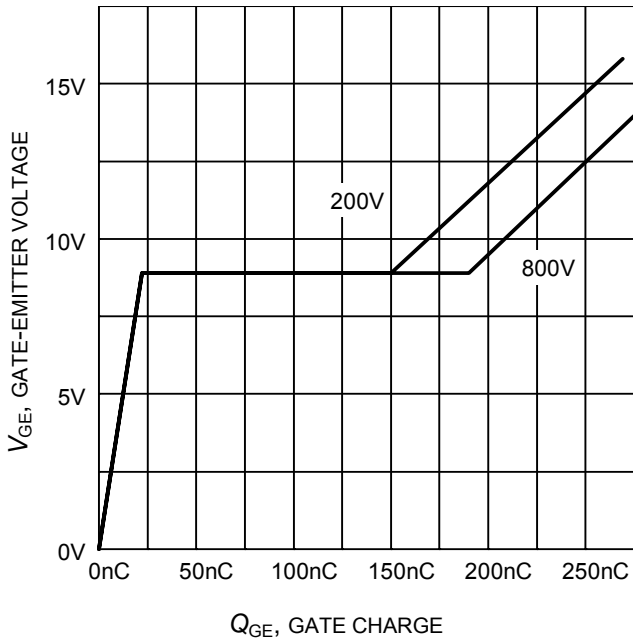


Figure 17. Typical gate charge
($I_C=30\text{ A}$)

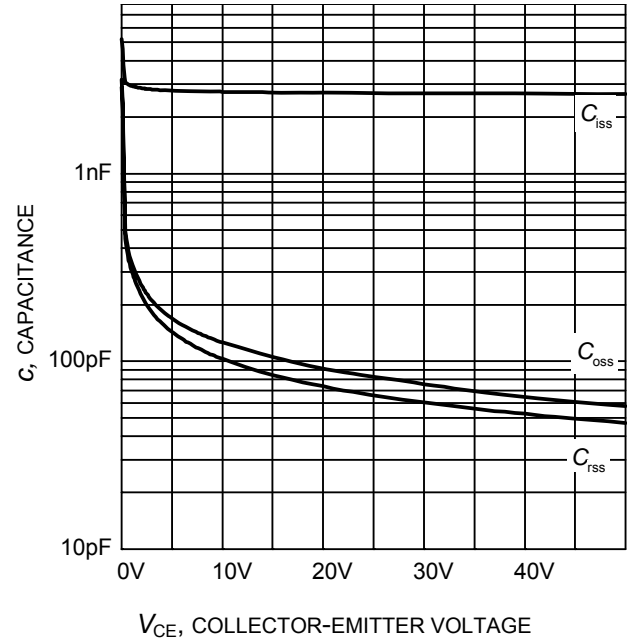


Figure 18. Typical capacitance as a function of collector-emitter voltage
($V_{GE}=0\text{V}$, $f = 1\text{ MHz}$)

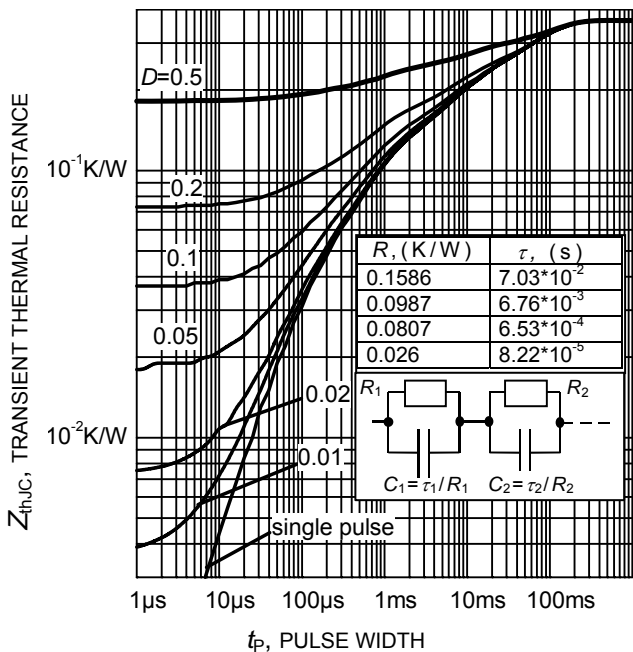


Figure 19. IGBT transient thermal impedance
($D = t_p / T$)

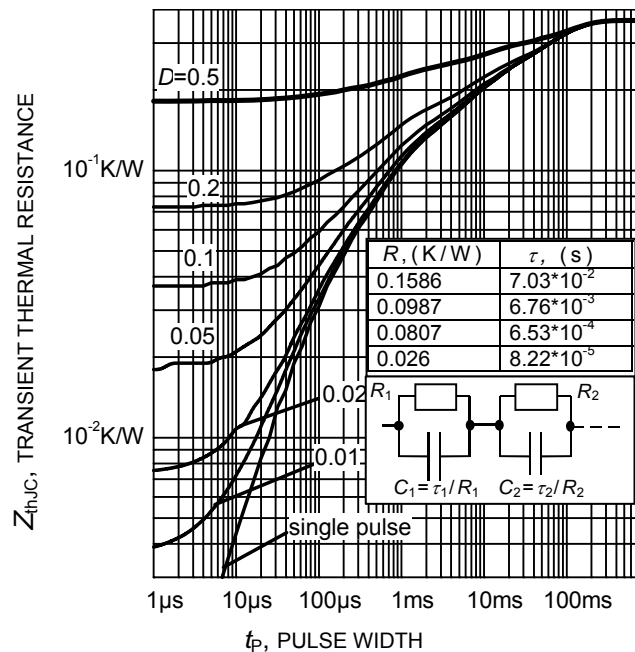


Figure 20. Diode transient thermal impedance as a function of pulse width
($D = t_p / T$)

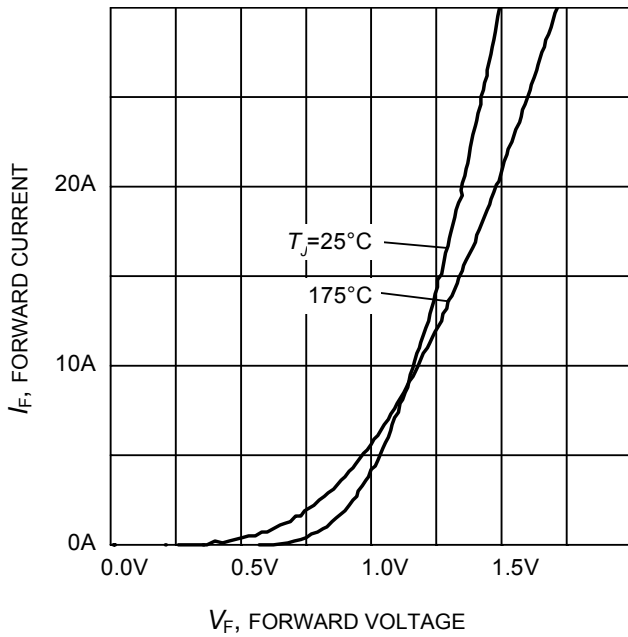


Figure 21. Typical diode forward current as a function of forward voltage

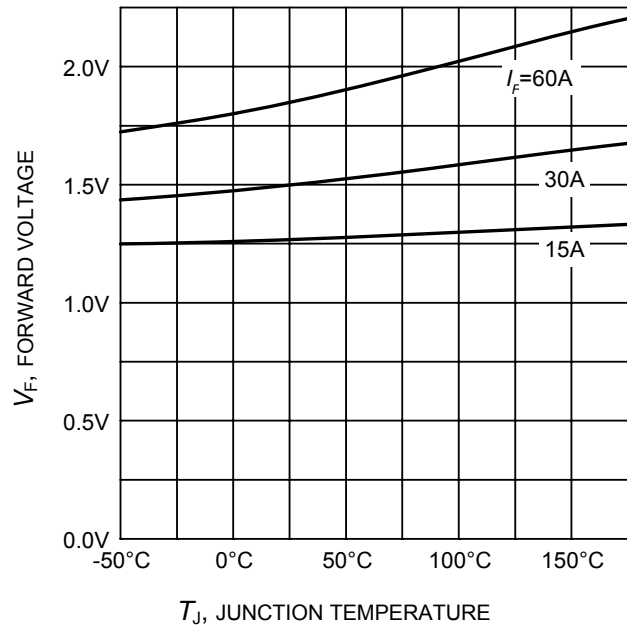
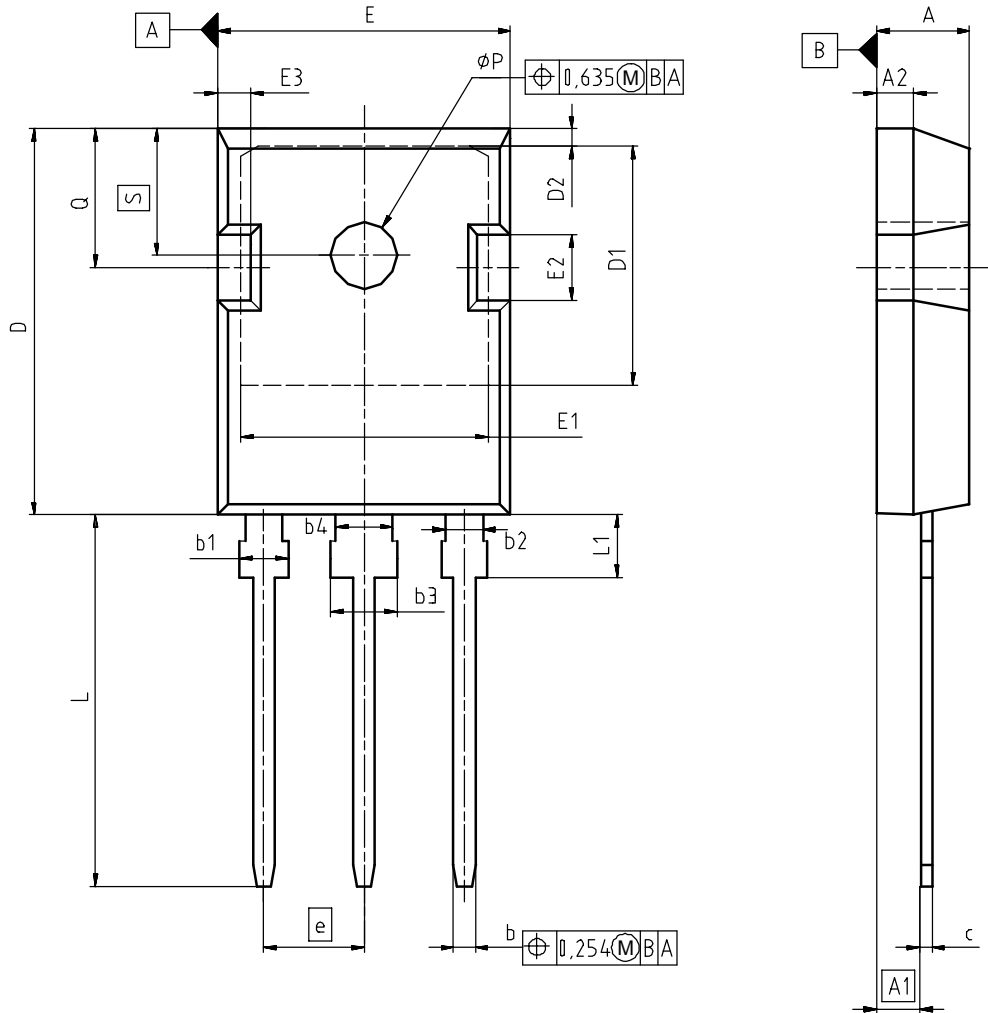


Figure 22. Typical diode forward voltage as a function of junction temperature

PG-TO247-3



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.16	0.193	0.203
A1	2.27	2.53	0.089	0.099
A2	1.85	2.11	0.073	0.083
b	1.07	1.33	0.042	0.052
b1	1.90	2.41	0.075	0.095
b2	1.90	2.16	0.075	0.085
b3	2.87	3.38	0.113	0.133
b4	2.87	3.13	0.113	0.123
c	0.55	0.68	0.022	0.027
D	20.82	21.10	0.820	0.831
D1	16.25	17.65	0.640	0.695
D2	1.05	1.35	0.041	0.053
E	15.70	16.03	0.618	0.631
E1	13.10	14.15	0.516	0.557
E2	3.68	5.10	0.145	0.201
E3	1.68	2.60	0.066	0.102
e	5.44		0.214	
N	3		3	
L	19.80	20.31	0.780	0.799
L1	4.17	4.47	0.164	0.176
$\varnothing P$	3.50	3.70	0.138	0.146
Q	5.49	6.00	0.216	0.236
S	6.04	6.30	0.238	0.248

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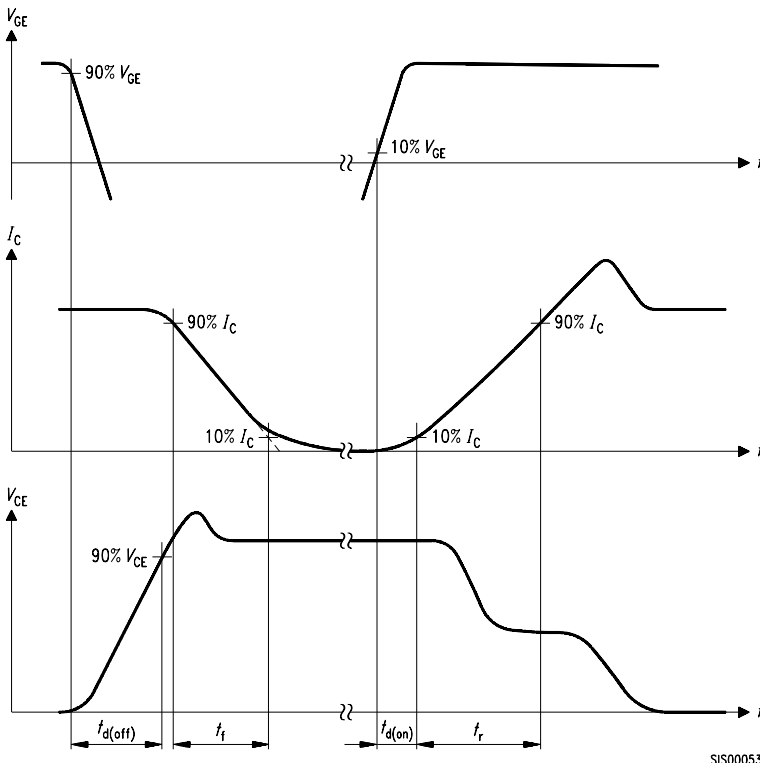


Figure A. Definition of switching times

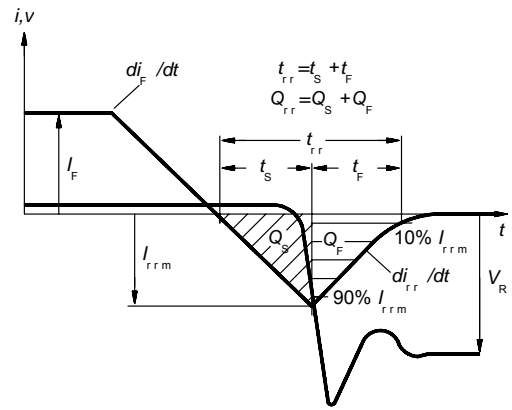


Figure C. Definition of diodes switching characteristics

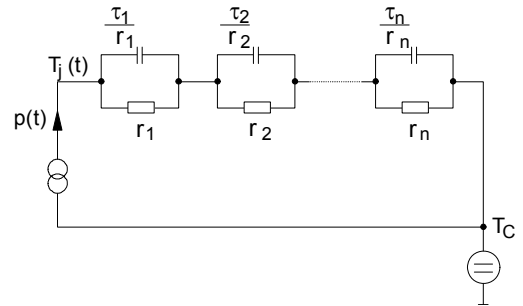


Figure D. Thermal equivalent circuit

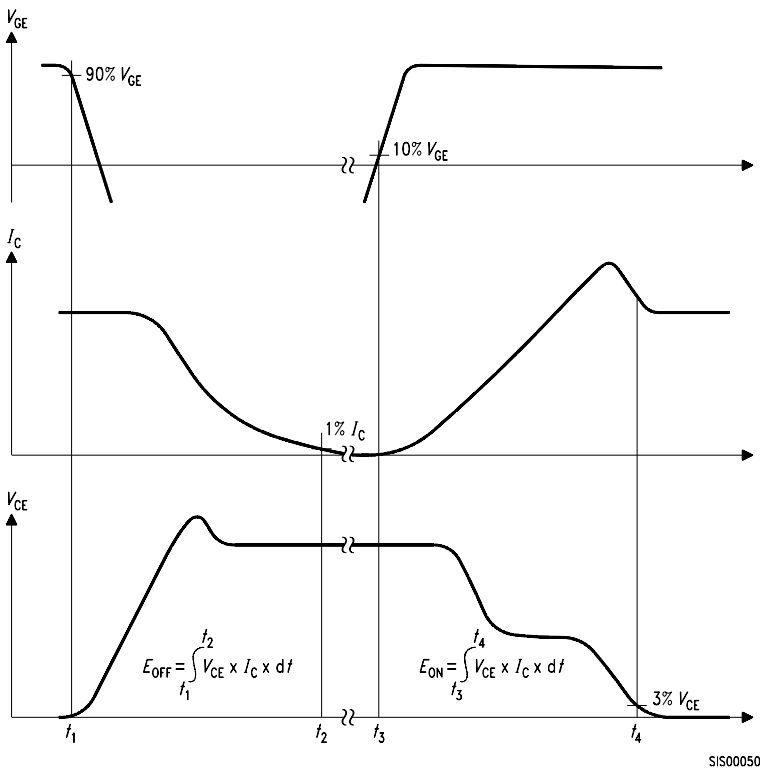


Figure B. Definition of switching losses

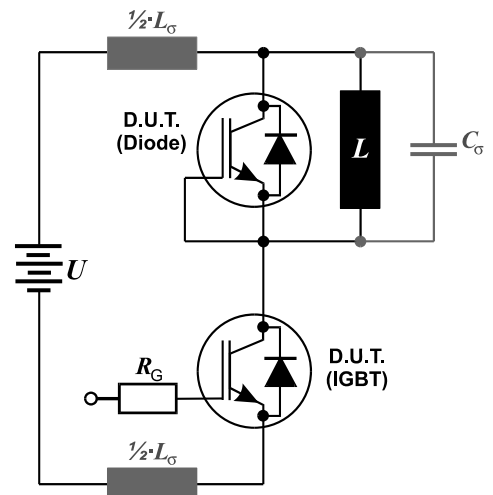


Figure E. Dynamic test circuit

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